

10EE764

## Seventh Semester B.E. Degree Examination, July/August 2022 VLSI Circuits and Design

Time: 3 hrs.

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Max. Marks:100

Note: Answer any FIVE full questions, selecting atleast TWO questions from each part.

## PART - A

- a. Explain the evolution of VLSI technology with respect to Moore's law. (08 Marks)
  b. Explain the working of nMOS enhancement type transistor for different regions of operation and draw its input and output characteristics. (12 Marks)
- a. With relevant diagrams, explain the N-well CMOS fabrication process. (10 Marks)
   b. Show that the pull-up and pull-down ratio of nMOS inverter driving another nMOS inverter
  - is 8:1. (10 Marks)
- 3 a. Explain the working of a CMOS inverter in different regions of operation with the help of transfer characteristics. (10 Marks)
  - b. Explain about latch up in CMOS circuits, what are the remedies to avoid latch up?

(10 Marks)

- 4 a. How will you represent wires, transistors and contract acts considering lambda based design rules? (08 Marks)
  - b. Draw the transistor level diagram and stick diagram of two way selector. (06 Marks)c. Draw the layout of two point nMOS NOR gate. (06 Marks)

## PART – B

- 5 a. Explain the operation of inverting and Non-inverting super buffers. (08 Marks)
   b. Define the scaling factor for i) gate area ii) gate capacitance iii) gate delay iv) channel resistance v) maximum operating frequency vi) saturation current. (12 Marks)
- 6 a. Explain about Dynamic CMOS logic, How can it be improved for cascading of logic (10 Marks)
  - b. Explain the bus arbitration logic and draw its stick diagram. (10 Marks)
- 7 a. Implement a 4-way multiplexer with nMOS switches and explain how can it be designed to operate as logic gates. (10 Marks)
  - b. Design a 4-bit addar element and implement the function of ALU with it. (10 Marks)
- 8 Write a short note on the following :
  - i)E-beam masks(05 Marks)ii)Pass transistor logic(05 Marks)iii)Sheet resistance(05 Marks)iv)Pseudo nMOS logic.(05 Marks)

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